

SWITCHING
N- AND P-CHANNEL POWER MOS FET

DESCRIPTION

The μ PA1793 is N- and P-Channel MOS Field Effect Transistors designed for Motor Drive application.

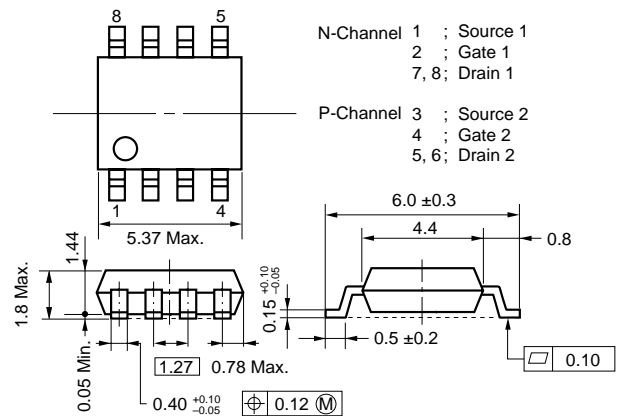
FEATURES

- Low on-state resistance
 N-Channel $R_{DS(on)1} = 69 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 4.5 \text{ V}$, $I_D = 1.5 \text{ A}$)
 $R_{DS(on)2} = 72 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 4.0 \text{ V}$, $I_D = 1.5 \text{ A}$)
 $R_{DS(on)3} = 107 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 2.5 \text{ V}$, $I_D = 1.0 \text{ A}$)
 P-Channel $R_{DS(on)1} = 115 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -4.5 \text{ V}$, $I_D = -1.5 \text{ A}$)
 $R_{DS(on)2} = 120 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -4.0 \text{ V}$, $I_D = -1.5 \text{ A}$)
 $R_{DS(on)3} = 190 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -2.5 \text{ V}$, $I_D = -1.0 \text{ A}$)
- Low input capacitance
 N-Channel $C_{iss} = 160 \text{ pF TYP.}$
 P-Channel $C_{iss} = 370 \text{ pF TYP.}$
- Built-in G-S protection diode
- Small and surface mount package (Power SOP8)

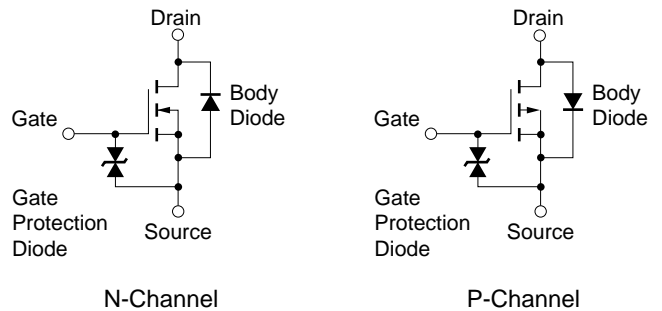
ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1793G	Power SOP8

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, All terminals are connected.)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	20	-20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	± 12	∓ 12	V
Drain Current (DC)	I _{D(DC)}	± 3	∓ 3	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	± 12	∓ 12	A
Total Power Dissipation (1 unit) ^{Note2}	P _T	1.7		W
Total Power Dissipation (2 units) ^{Note2}	P _T	2.0		W
Channel Temperature	T _{ch}	150		°C
Storage Temperature	T _{stg}	-55 to +150		°C

Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

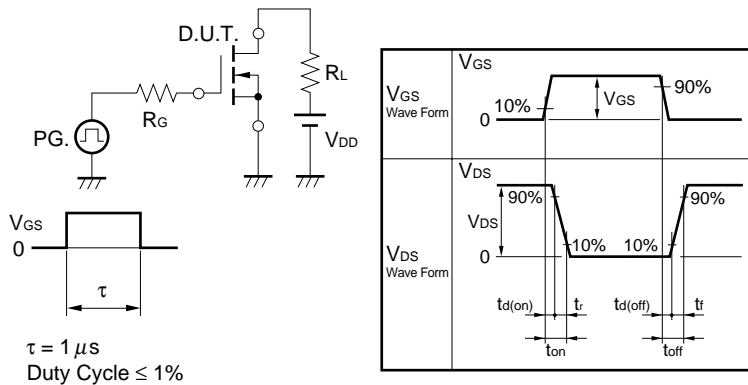
2. Mounted on ceramic substrate of 5500 mm² × 2.2 mm, T_A = 25°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C, All terminals are connected.)

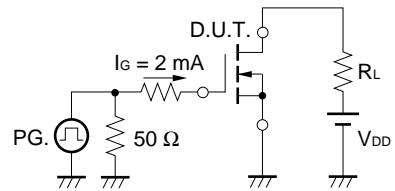
A) N-Channel

Characteristic	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	0.5	1.0	1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 1.5 A	1.0			S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 4.5 V, I _D = 1.5 A		55	69	mΩ
	R _{DS(on)2}	V _{GS} = 4.0 V, I _D = 1.5 A		57	72	mΩ
	R _{DS(on)3}	V _{GS} = 2.5 V, I _D = 1.0 A		78	107	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V		160		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		60		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		40		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10 V, I _D = 1.5 A		17		ns
Rise Time	t _r	V _{GS} = 4.0 V		50		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		86		ns
Fall Time	t _f			80		ns
Total Gate Charge	Q _G	V _{DD} = 16 V		3.1		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 4.0 V		0.7		nC
Gate to Drain Charge	Q _{GD}	I _D = 3.0 A		1.4		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 3.0 A, V _{GS} = 0 V		0.86		V
Reverse Recovery Time	t _{rr}	I _F = 3 A, V _{GS} = 0 V		70		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 50 A/μs		12		nC

TEST CIRCUIT 1 SWITCHING TIME



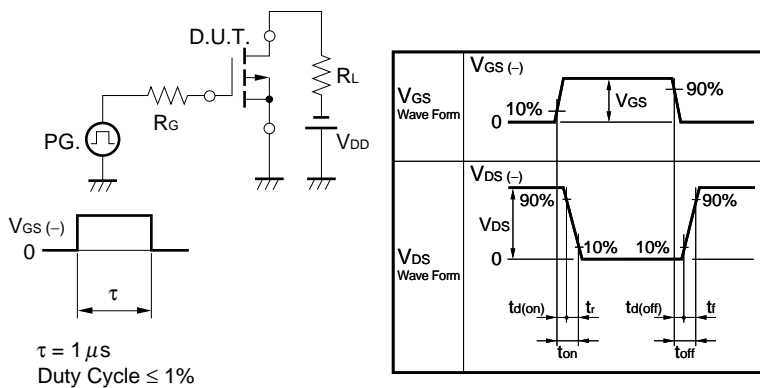
TEST CIRCUIT 2 GATE CHARGE



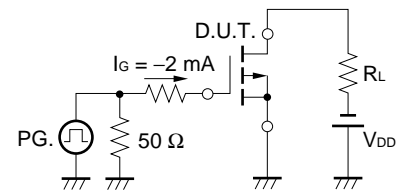
B) P-Channel

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-10	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \mp 12\text{ V}, V_{DS} = 0\text{ V}$			∓ 10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-0.5	-1.0	-1.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -1.5\text{ A}$	1.0			S
Drain to Source On-state Resistance	$R_{DS(on)1}$	$V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$		75	115	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS} = -4.0\text{ V}, I_D = -1.5\text{ A}$		80	120	$\text{m}\Omega$
	$R_{DS(on)3}$	$V_{GS} = -2.5\text{ V}, I_D = -1.0\text{ A}$		116	190	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}$		370		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$		110		pF
Reverse Transfer Capacitance	C_{rss}	$f = 1\text{ MHz}$		40		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, I_D = -1.5\text{ A}$		120		ns
Rise Time	t_r	$V_{GS} = -4.0\text{ V}$		260		ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 10\ \Omega$		410		ns
Fall Time	t_f			360		ns
Total Gate Charge	Q_G	$V_{DD} = -10\text{ V}$		3.4		nC
Gate to Source Charge	Q_{GS}	$V_{GS} = -4.0\text{ V}$		1.3		nC
Gate to Drain Charge	Q_{GD}	$I_D = -3.0\text{ A}$		1.6		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 3.0\text{ A}, V_{GS} = 0\text{ V}$		0.86		V
Reverse Recovery Time	t_{rr}	$I_F = 3\text{ A}, V_{GS} = 0\text{ V}$		24		ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 10\text{ A}/\mu\text{s}$		1.5		nC

TEST CIRCUIT 1 SWITCHING TIME



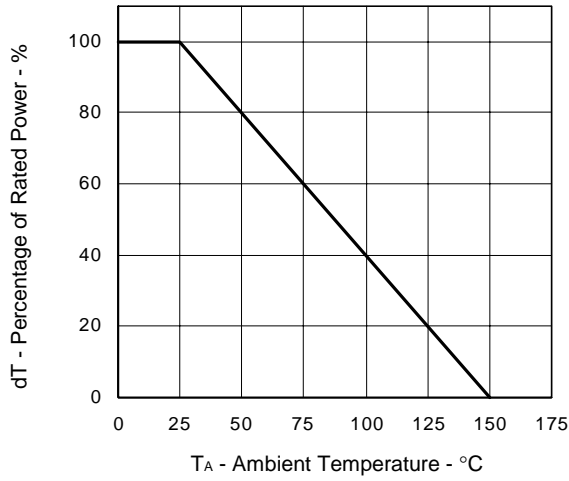
TEST CIRCUIT 2 GATE CHARGE



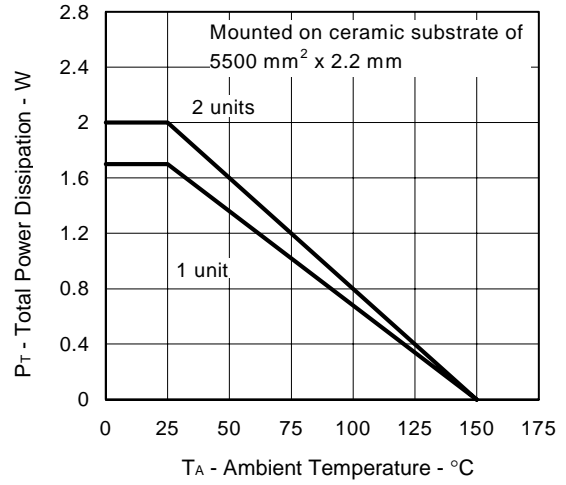
TYPICAL CHARACTERISTICS (T_A = 25°C)

A) N-Channel

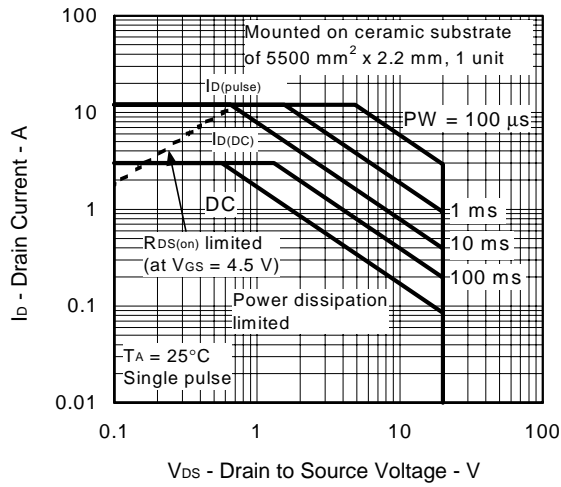
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



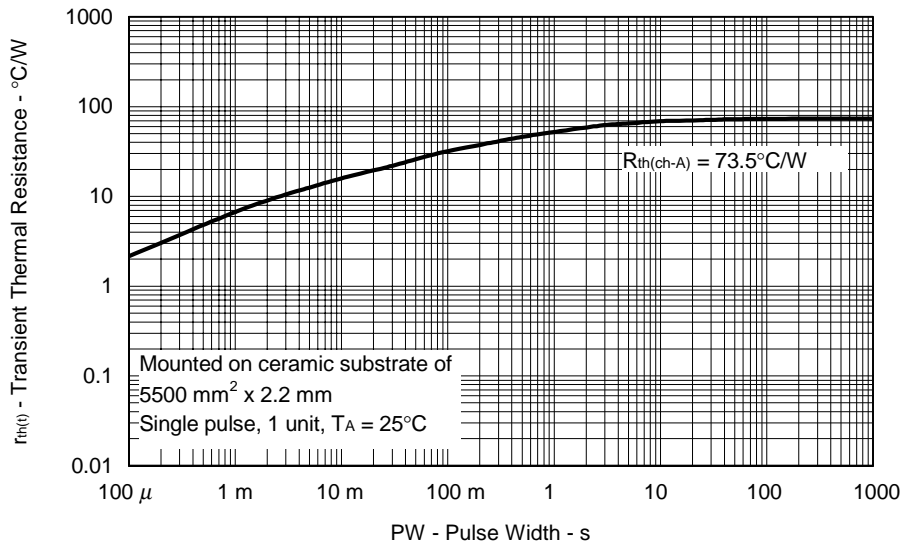
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



FORWARD BIAS SAFE OPERATING AREA

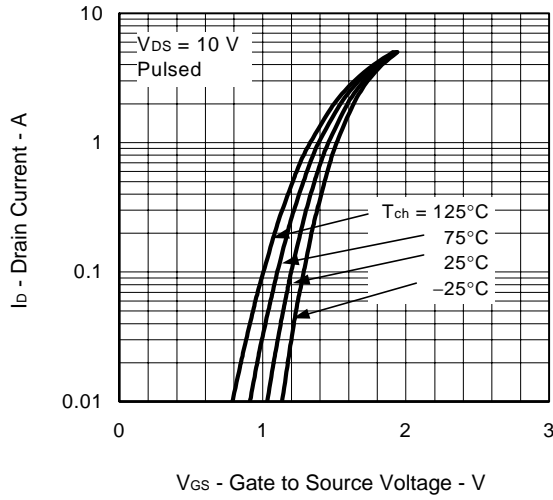


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

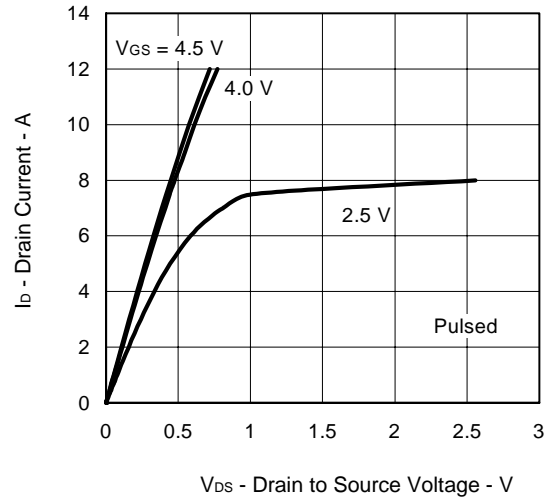


A) N-Channel

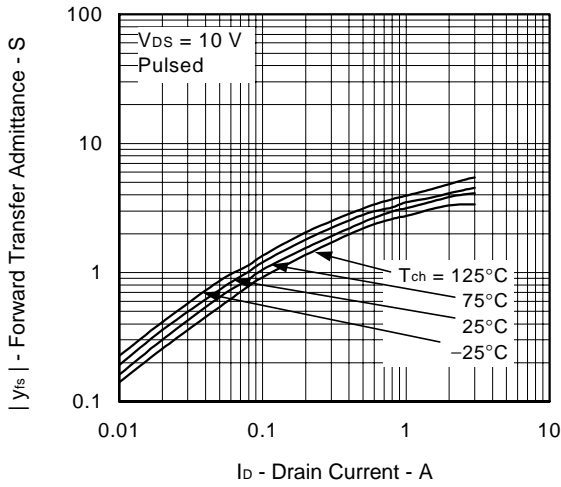
FORWARD TRANSFER CHARACTERISTICS



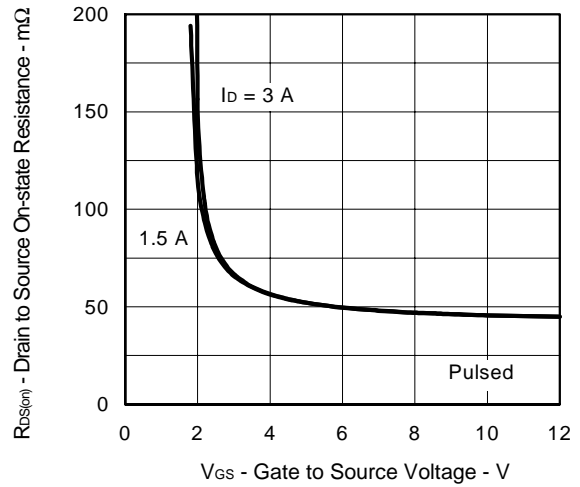
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



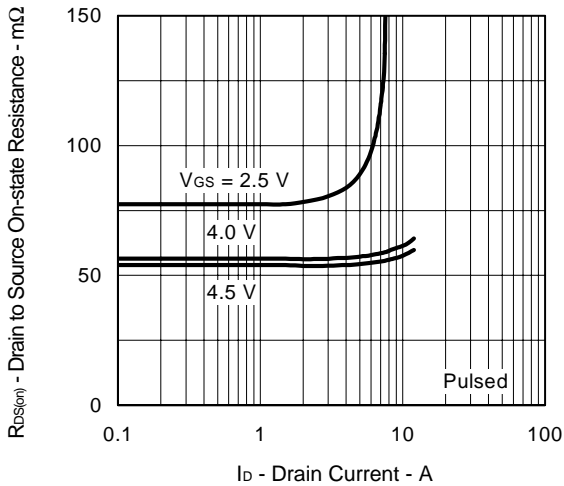
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



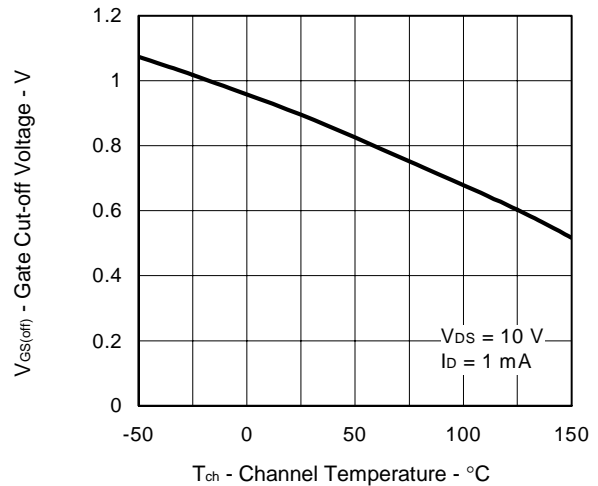
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

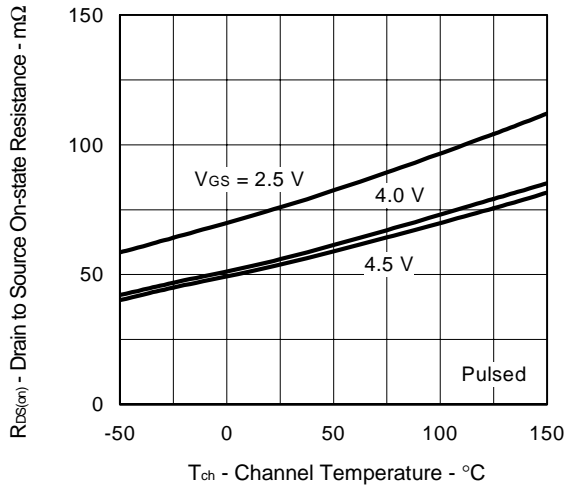


GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

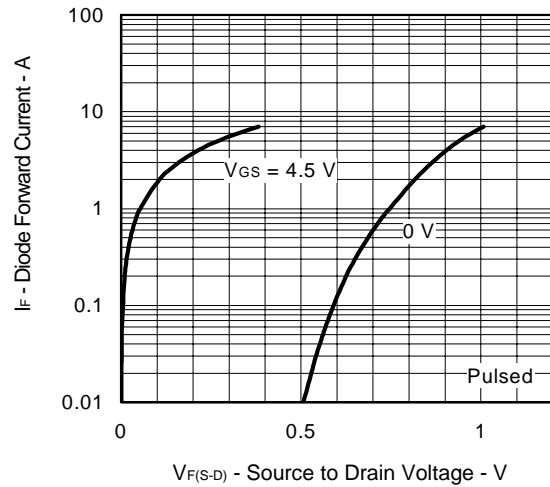


A) N-Channel

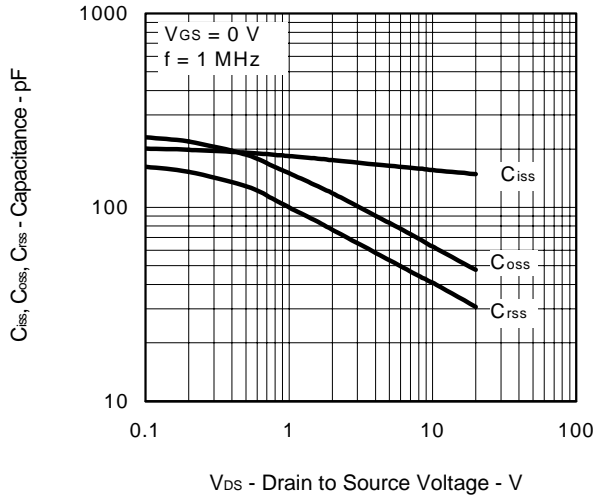
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



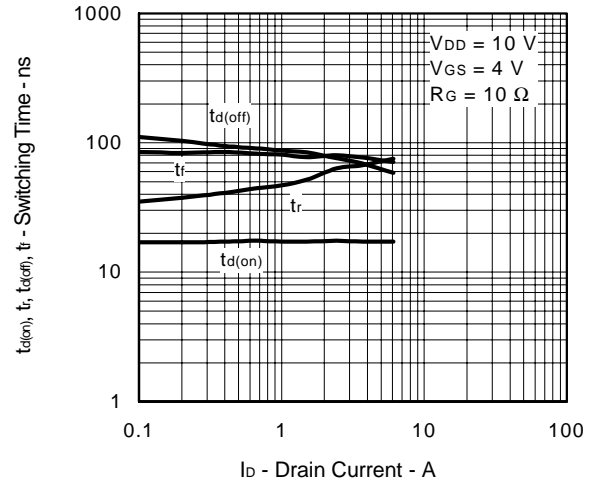
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



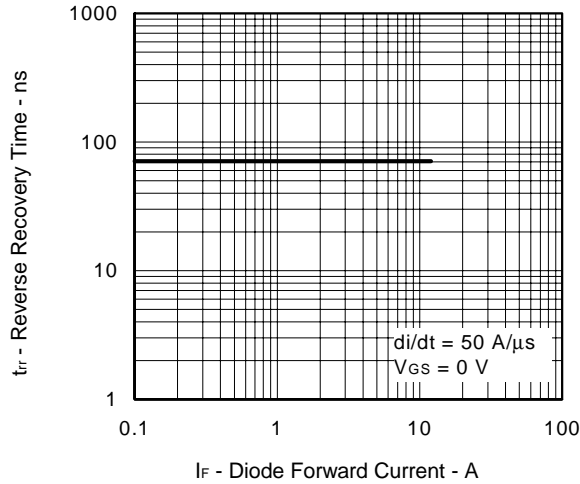
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



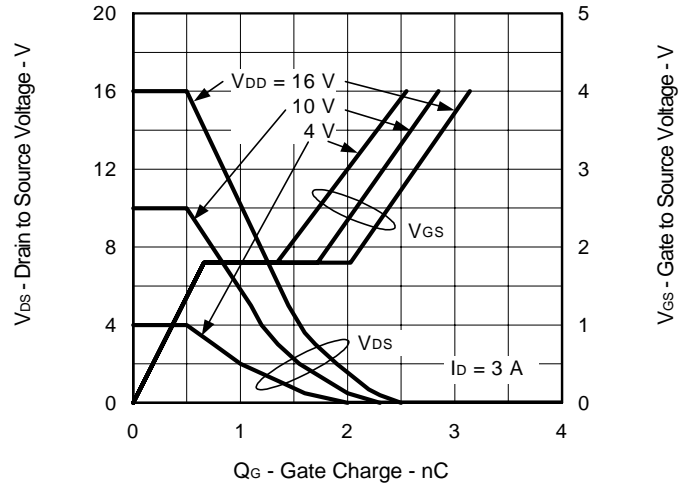
SWITCHING CHARACTERISTICS



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

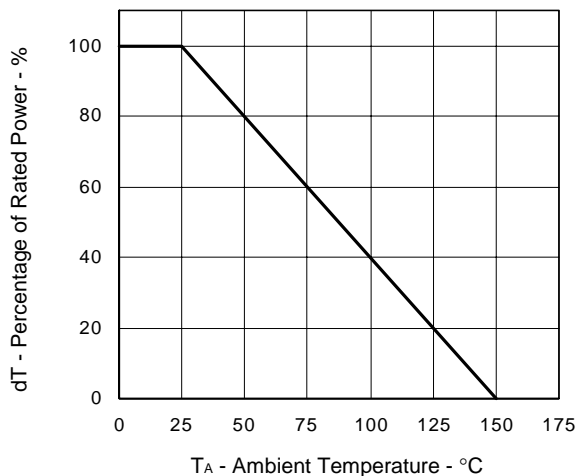


DYNAMIC INPUT/OUTPUT CHARACTERISTICS

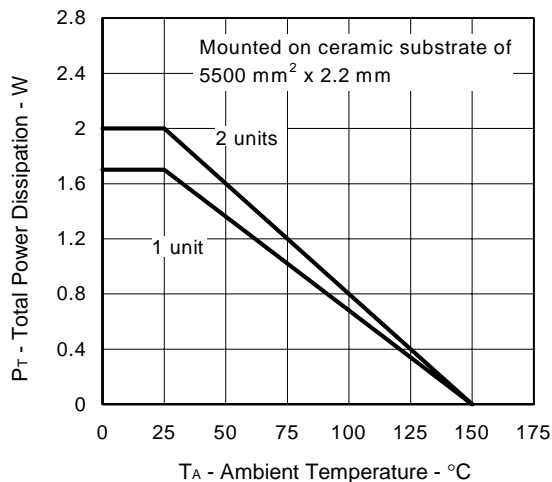


B) P-Channel

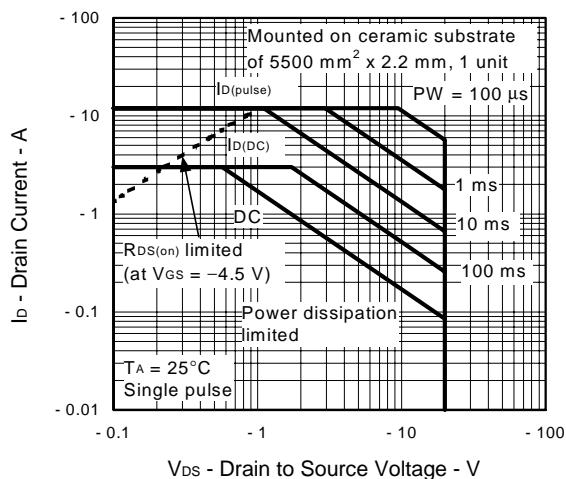
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



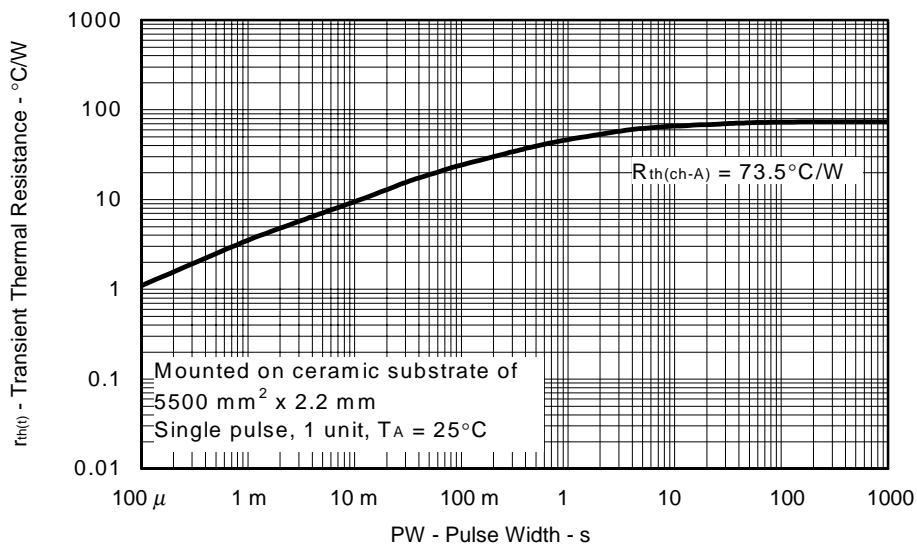
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



FORWARD BIAS SAFE OPERATING AREA

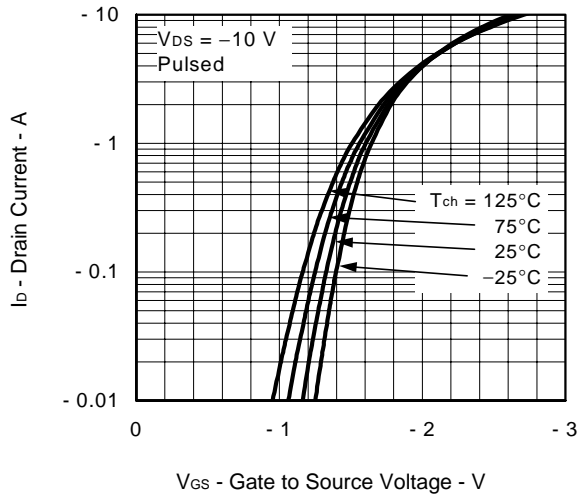


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

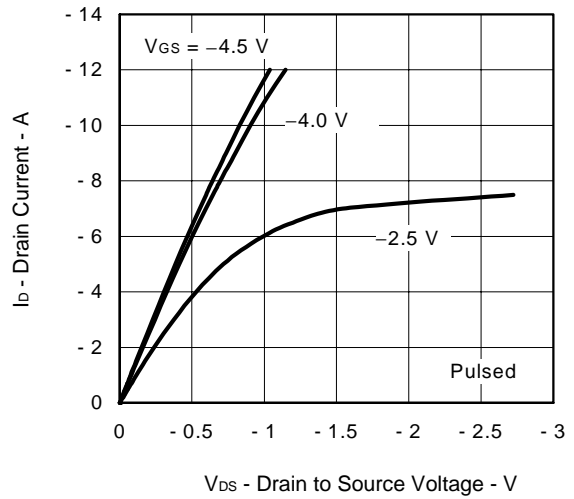


B) P-Channel

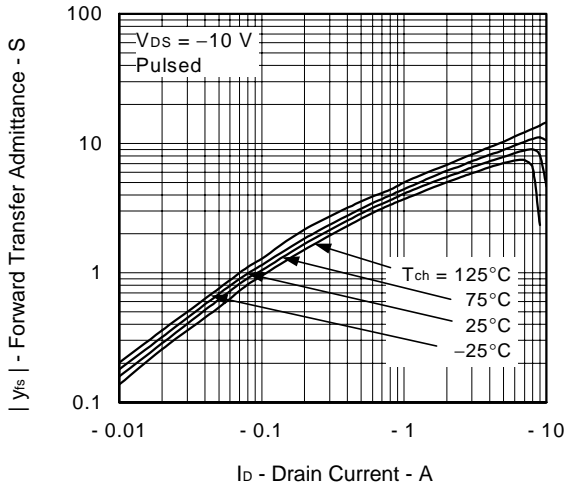
FORWARD TRANSFER CHARACTERISTICS



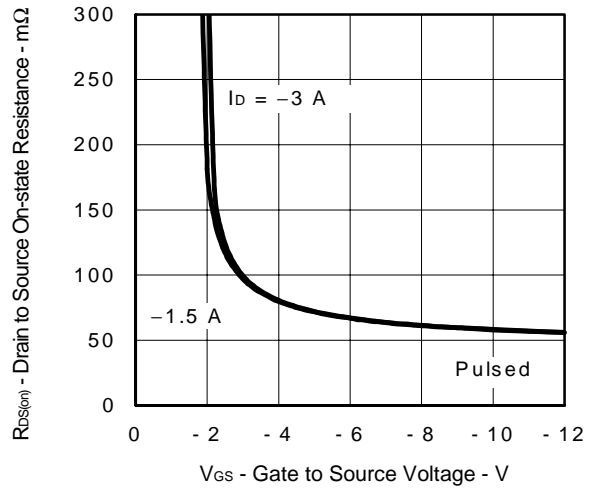
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



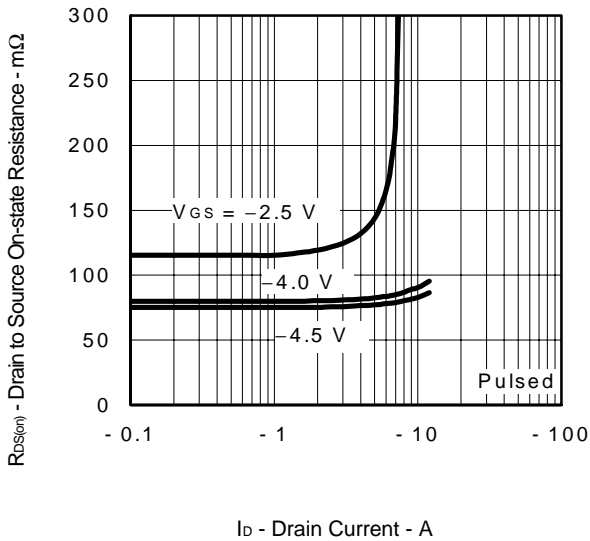
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



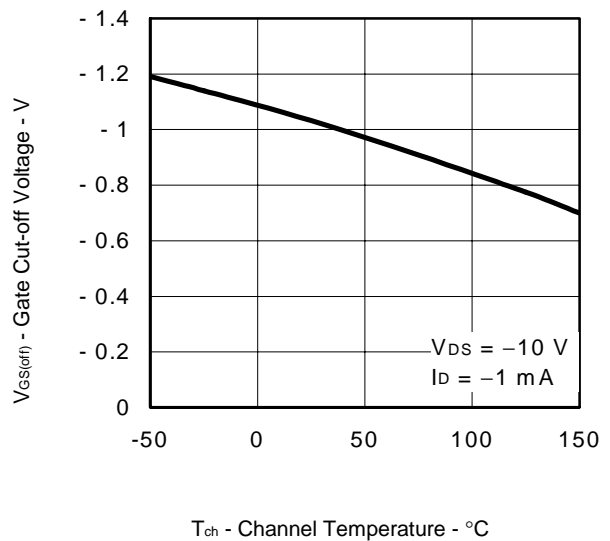
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

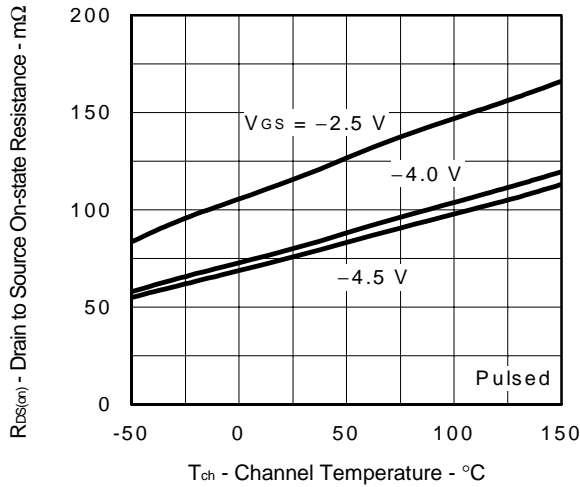


GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

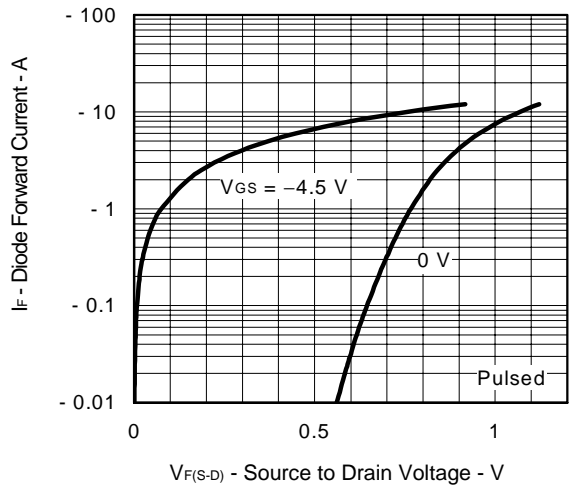


) P-Channel

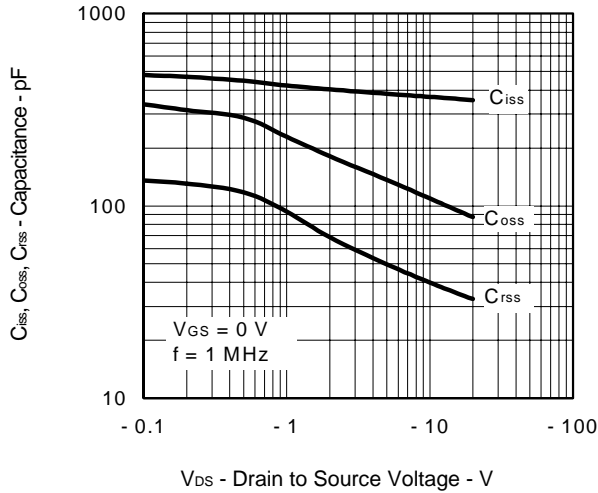
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



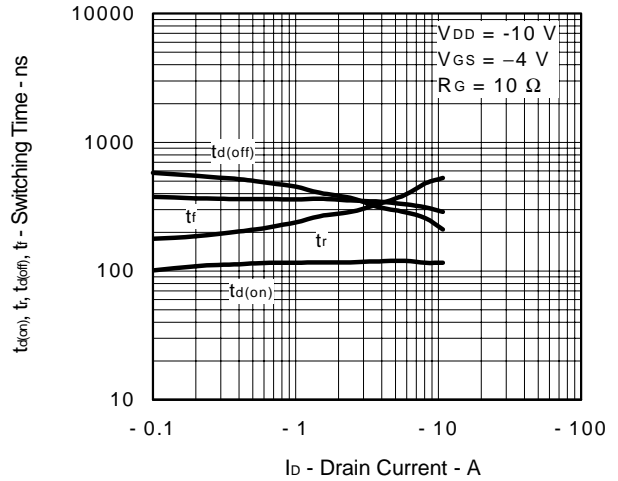
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



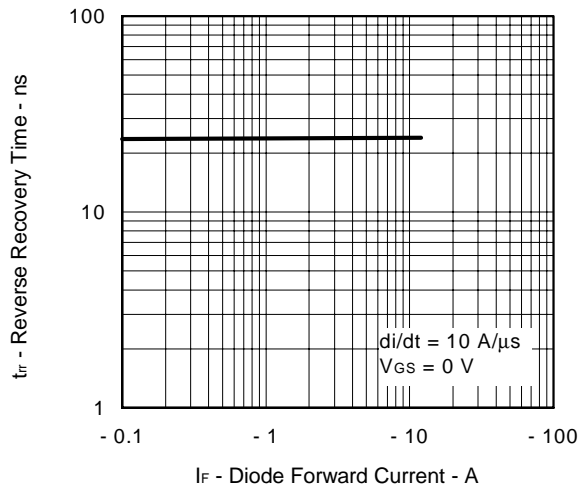
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



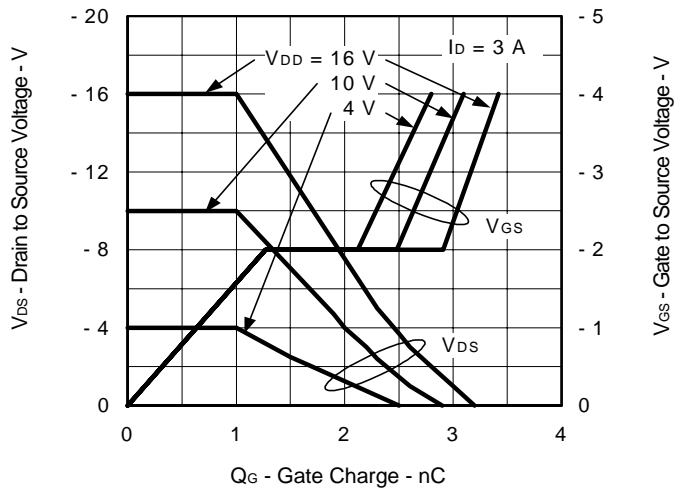
SWITCHING CHARACTERISTICS



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



[MEMO]

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